TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ($L^2-\pi$ -MOSIV)

2SJ312

DC–DC Converter, Relay Drive and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance $: RDS (ON) = 80 \text{ m}\Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 8.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = -100 \ \mu A \ (max) \ (V_{DS} = -60 \ V)$
- Enhancement mode : $V_{th} = -0.8 \sim -2.0 \text{ V} (V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	-60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	-60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-14	А	
	Pulse(Note 1)	I _{DP}	-56		
Drain power dissipation (Tc = 25°C)		PD	40	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

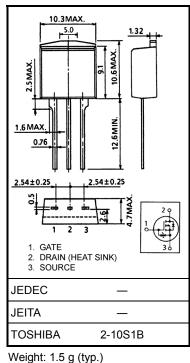
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

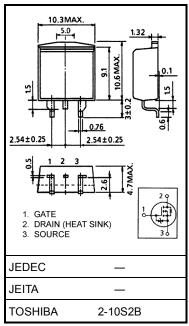
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.







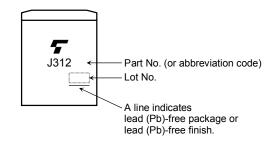
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V		—	±10	μA
Drain cut-off cu	rrent	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$		_	-100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-60	—		V
Gate threshold	voltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V
Drain-source ON resistance		R _{DS (ON)}	V _{GS} = -4 V, I _D = -5 A		130	190	mΩ
			$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -7 \text{ A}$	_	80	120	
Forward transfe	r admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -7 \text{ A}$	5.0	8.0	-	S
Input capacitance	ce	C _{iss}			1200		
Reverse transfer capacitance		C _{rss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	220	—	pF
Output capacitance		Coss		_	550	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{0V}{\xrightarrow{-10V}} \stackrel{I_{D} = -7A}{\xrightarrow{V_{DD} \Rightarrow -30V}} V_{OUT}$ $R_{L} = 4.3\Omega$ $V_{DD} = -30V$ $Duty \le 1\%, t_{W} = 10\mu s$	_	20	_	. ns
	Turn-on time	t _{on}		_	30	_	
	Fall time	t _f		_	25	_	
	Turn-off time	t _{off}		_	100	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	45	_	nC
Gate-source charge		Q _{gs}	V _{DD} ≈ -48 V, V _{GS} = -10 V, I _D = -14 A	_	30	_	
Gate-drain ("miller") charge		Q _{gd}			15	_	

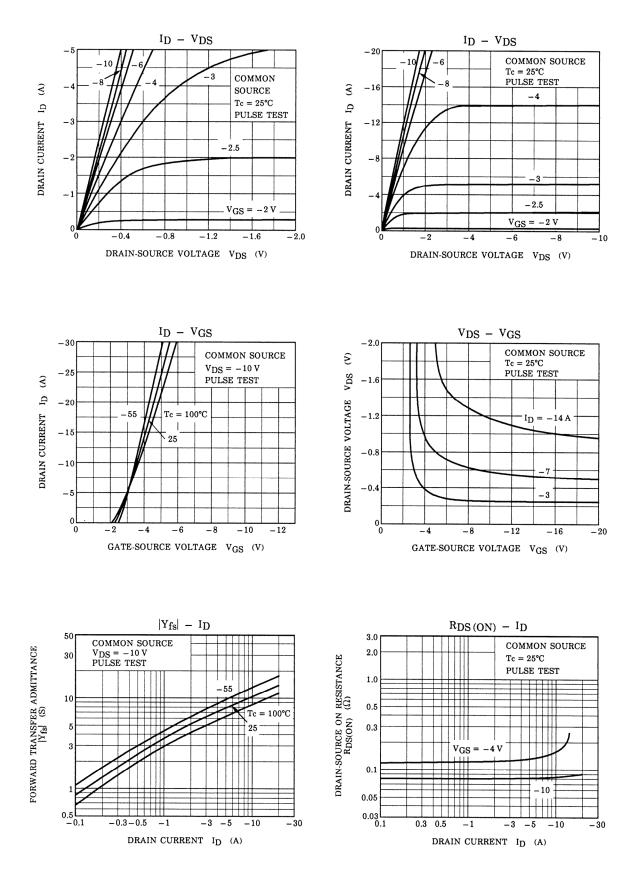
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	-14	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	-56	A
Forward voltage (diode)	V _{DSF}	I _{DR} = -14 A, V _{GS} = 0 V	_	_	1.7	V
Reverse recovery time	trr	I _{DR} = -14 A, V _{GS} = 0 V		110	—	ns
Reverse recovery charge	Qrr	dI _{DR} / dt = 50 A / μs	I	0.18	—	μC

Marking



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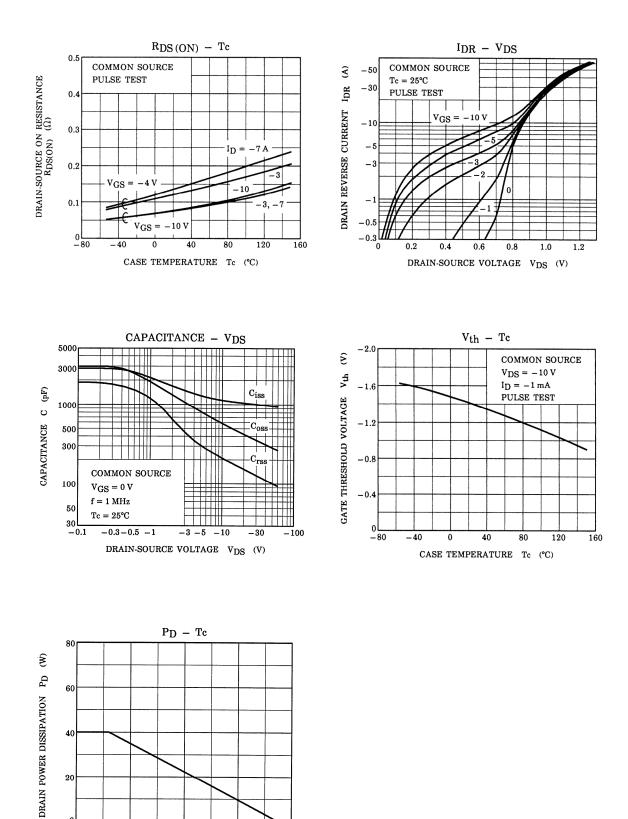
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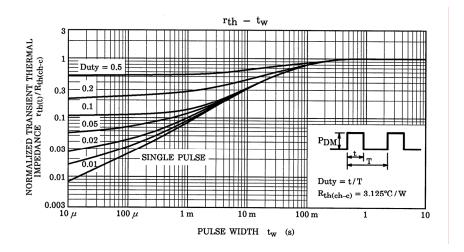
80

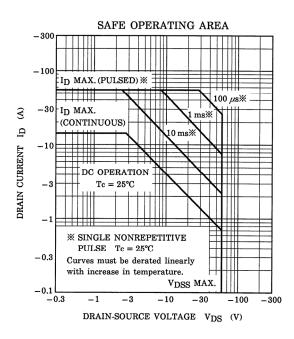
CASE TEMPERATURE Tc (°C)

120

160







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